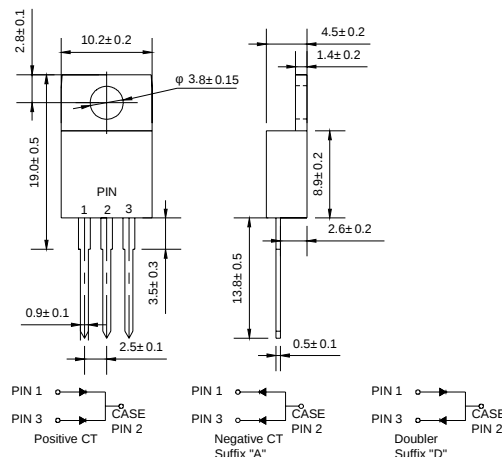




TO-220AB



Dimensions in millimeters

Features

- ◇ High surge capacity.
- ◇ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.
- ◇ Metal silicon junction, majority carrier conduction.
- ◇ High current capacity, low forward voltage drop.
- ◇ Guard ring for over voltage protection.

Mechanical Data

- ◇ Case: JEDEC TO-220AB, molded plastic body
- ◇ Polarity: As marked
- ◇ Position: Any
- ◇ Weight: 0.071ounce, 2.006 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

		MBR 2530CT	MBR 2535CT	MBR 2540CT	MBR 2545CT	MBR 2550CT	MBR 2560CT	MBR 2580CT	MBR 25100CT	UNITS
Maximum recurrent peak reverse voltage	V _{RRM}	30	35	40	45	50	60	80	100	V
Maximum RMS Voltage	V _{RMS}	21	25	28	32	35	42	56	70	V
Maximum DC blocking voltage	V _{DC}	30	35	40	45	50	60	80	100	V
Maximum average forw ard total device rectified current @T _C = 130°C	I _{F(AV)}	30								A
Peak forw ard surge current 8.3ms single half sine-w ave superimposed on rated load	I _{FSM}	150								A
Maximum forward voltage (Note 1)	V _F	-				0.75		0.85		V
(I _F =15A,T _C =25 °C)		-				0.65		-		
(I _F =15A,T _C =125 °C)		0.82				-		-		
(I _F =30A,T _C =25°C)		0.73				-		-		
Maximum reverse current @T _C =25°C	I _R	0.2				1.0				m A
at rated DC blocking voltage @T _C =125°C		40				50				
Maximum thermal resistance (Note2)	R _{θJC}	1.5								°C/W
Operating junction temperature range	T _J	- 55 ---- + 150								°C
Storage temperature range	T _{STG}	- 55 ---- + 150								°C

NOTE: 1. Pulse test: 300μs pulse width, 1% duty cycle.

2. Thermal resistance from junction to case.

Ratings AND Characteristic Curves

FIG.1 – PEAK FORWARD SURGE CURRENT

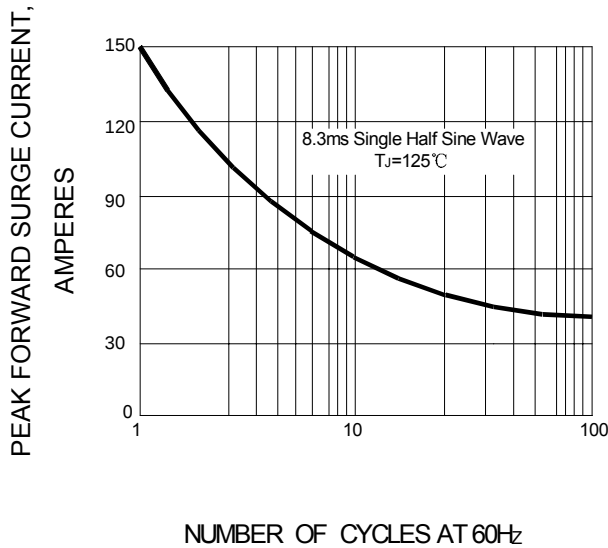


FIG.2 – FORWARD DERATING CURVE

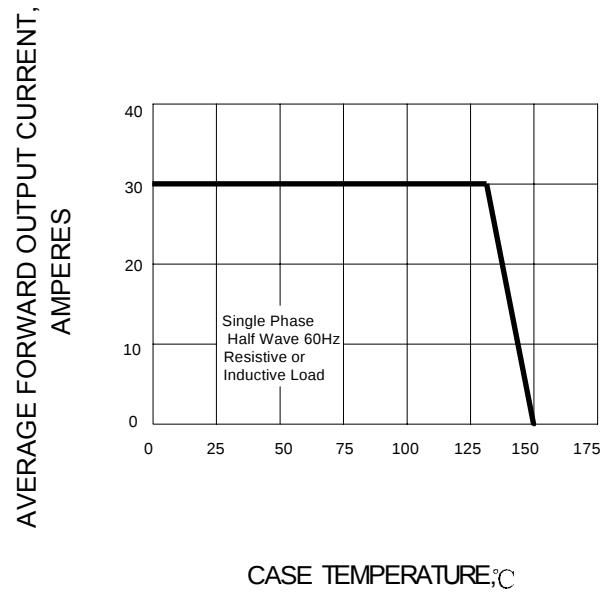


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

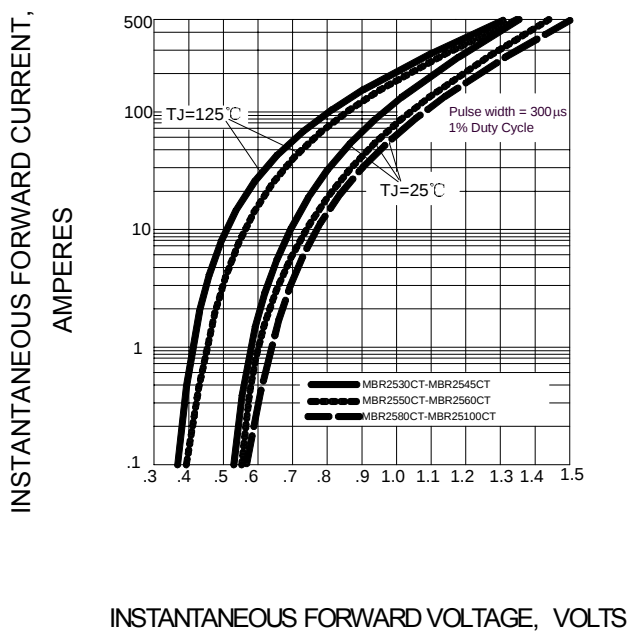


FIG.4 – TYPICAL REVERSE CHARACTERISTIC

